



DMP2225L

#### P-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

#### **Features**

Low On-Resistance:

$$\begin{split} R_{DS(ON)} < 110 m\Omega & @V_{GS} = -4.5V \\ R_{DS(ON)} < 225 m\Omega & @V_{GS} = -2.5V \end{split}$$

- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 2)
- "Green" Device (Note 4)
- Qualified to AEC-Q101 Standards for High Reliability

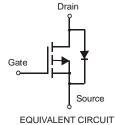
#### **Mechanical Data**

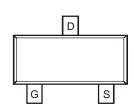
- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.008 grams (approximate)





TOP VIEW





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TOP VIEW

# **Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Ch	aracteristic		Symbol	Value	Units
Drain-Source Voltage			$V_{DSS}$	-20	V
Gate-Source Voltage			$V_{GSS}$	±12	V
Drain Current (Note 1)	Steady State	$T_A = 25$ °C $T_A = 70$ °C	I <sub>D</sub>	-2.6 -2	А
Pulsed Drain Current (Note 3)			I <sub>DM</sub>	8	A

### **Thermal Characteristics**

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 1)	P <sub>D</sub>	1.08	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = 25°C (Note 1)	$R_{ heta JA}$	115	°C/W
Operating and Storage Temperature Range	T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

Notes:

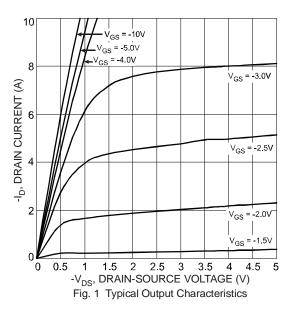
- 1. Device mounted on FR-4 PCB.  $t \le 5$  sec.
- 2. No purposefully added lead.
- 3. Pulse width  $\leq 10 \mu S$ , Duty Cycle  $\leq 1\%$ .
- 4. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.

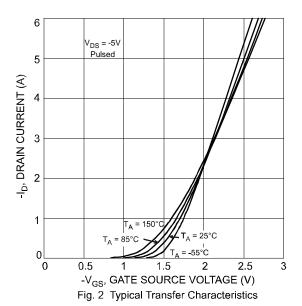


# Electrical Characteristics @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition			
OFF CHARACTERISTICS (Note 5)									
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20		_	V	$V_{GS} = 0V, I_D = -250\mu A$			
Zero Gate Voltage Drain Current	I <sub>DSS</sub>		_	-800	nA	$V_{DS} = -20V, V_{GS} = 0V$			
On-State Drain Current	l= .a.n	-6			Α	$V_{DS} \le -5V$ , $V_{GS} = -4.5V$			
On-State Brain Gunent	I <sub>D(ON)</sub>	-3	_			$V_{DS} \le -5V$ , $V_{GS} = -2.5V$			
Gate-Source Leakage	lass		_	±80	nA	$V_{GS} = \pm 12V$ , $V_{DS} = 0V$			
Gale-Source Leakage	I <sub>GSS</sub>			±800		$V_{GS} = \pm 15V, V_{DS} = 0V$			
ON CHARACTERISTICS (Note 5)	ON CHARACTERISTICS (Note 5)								
Gate Threshold Voltage	$V_{GS(th)}$	-0.62	-0.89	-1.25	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$			
Static Drain-Source On-Resistance	R <sub>DS</sub> (ON)	_	80	110	11177	$V_{GS} = -4.5V, I_D = -2.6A$			
Static Dialii-Source Off-Resistance			165	225		$V_{GS} = -2.5V, I_{D} = -2.0A$			
Forward Transfer Admittance	Y <sub>fs</sub>	_	4	_	S	$V_{DS} = -5V, I_{D} = -2.6A$			
Diode Forward Voltage (Note 5)	V <sub>SD</sub>	_	_	-1.26	V	$V_{GS} = 0V, I_{S} = -2.6A$			
DYNAMIC CHARACTERISTICS									
Input Capacitance	C <sub>iss</sub>		250		pF	V 40V V 0V			
Output Capacitance	Coss	_	88	_	pF	$V_{DS} = -10V, V_{GS} = 0V$ - f = 1.0MHz			
Reverse Transfer Capacitance	C <sub>rss</sub>	_	58	_	pF	1 = 1.000112			
Gate Resistance	Rg	_	12	16	Ω	$V_{GS} = 0V$ , $V_{DS} = 0V$ , $f = 1MHz$			
Total Gate Charge	Qg	_	4.3	5.3		V 45V V 10V			
Gate-Source Charge	Q <sub>gs</sub>	_	0.9	_	nC	$V_{GS} = -4.5V, V_{DS} = -10V,$ $I_{D} = -2.7A$			
Gate-Drain Charge	Q <sub>gd</sub>		2.1			ID = -2.1 A			

Notes: 5. Short duration pulse test used to minimize self-heating effect.







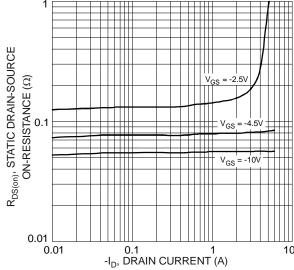


Fig. 3 On-Resistance vs. Drain Current and Gate Voltage

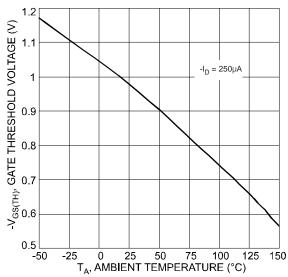


Fig. 5 Gate Threshold Voltage vs. Ambient Temperature

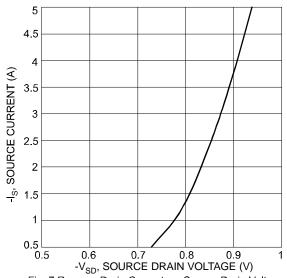
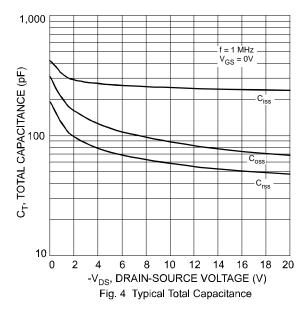
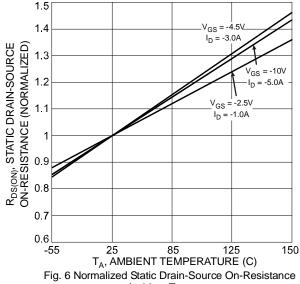


Fig. 7 Reverse Drain Current vs. Source-Drain Voltage





vs. Ambient Temperature

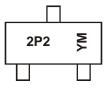


### Ordering Information (Note 6)

Part Number	Case	Packaging
DMP2225L-7	SOT-23	3000/Tape & Reel

Notes: 6. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

## **Marking Information**



2P2 = Product Type Marking Code YM = Date Code Marking

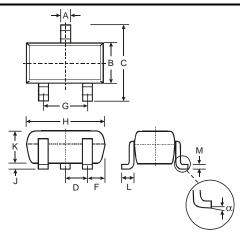
Y = Year ex: V = 2008 M = Month ex: 9 = Senter

M = Month ex: 9 = September

Date Code Key

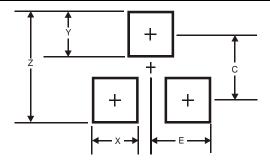
Year	2008		2009	2010		2011	2012	!	2013	2014		2015
Code	V		W	Х		Υ	Z		Α	В		С
Month	Jan	Feb	Mar	Apr	Ma	y Jun	Jul	Aug	g Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

# Package Outline Dimensions



SOT-23					
Dim	Min	Max			
Α	0.37	0.51			
В	1.20	1.40			
С	2.30	2.50			
D	0.89	1.03			
F	0.45	0.60			
G	1.78	2.05			
Н	2.80	3.00			
J	0.013	0.10			
K	0.903	1.10			
L	0.45	0.61			
M	0.085	0.180			
α	0°	8°			
All Dimensions in mm					

# **Suggested Pad Layout**



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35

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